

Input Impedance – It is calculated based on the incremental model of the LNA as shown in Fig. 2. Assuming that $i_1 = -i_2$, $v_{gs1} = -v_{gs2}$ and $c_{gs1} = c_{gs2}$, the input impedance is given by,

$$Z_{in} = \frac{v_x}{i_x} = sL_S - 2sM \frac{2sM(2sC_{gs1} + g_{m1})}{1 + 2sL_1(2sC_{gs1} + g_{m1})} \quad (1)$$

where M is the mutual inductance: $M = k\sqrt{L_S L_1} = k\sqrt{L_S L_2}$. Assuming that $L_S = 2L_1$, $g_{m1} \gg |2sC_{gs1}|$ and $g_{m1} = 1/R_S$, Z_{in} can be simplified as,

$$Z_{in} = \frac{2sL_1(R_S + 2(1 - 2k^2)sL_1)}{R_S + 2sL_1} \quad (2)$$

Eq. (2) can be used to determine the input resonant frequency. With $Z_{in} = R_S$, the resonant frequency is obtained,

$$f_0 \approx \frac{1}{2\sqrt{2k^2 - 1}} \frac{R_S}{L_1} \quad (3)$$

Eq. (3) reveals that f_0 is independent of C_{gs} since v_{gs} is determined by the balun and is directly applied to the gate-source terminals of M_1 and M_2 . The input impedance is relatively wideband because the Q is low, the same as CCC-CGLNA. It also implies that the impedance matching is insensitive to the input parasitic capacitance.

Voltage Gain – This LNA can be partitioned into 3 stages. Each features an internal voltage gain. If the channel length modulation is neglected, the final gain of the 3 stages can be determined independently. The gain of the 1st stage corresponds to the gain of the balun. Considering Fig. 2 again and assuming that $g_{m1} \gg |2sC_{gs1}|$, and $L_S = 2L_1$, the gain of the 1st stage can be obtained,

$$\frac{v_{gs1}}{v_x} = \frac{\sqrt{2}k}{1 + 2g_{m1}(1 - 2k^2)L_1 s} \quad (4)$$

The balun voltage gain has a pole at around $-1/2g_{m1}L_1$ that must be apart from the resonant frequency desired for the LNA. Neglecting C_{gs} and let $v_{gs3} = -v_{gs4} = v_{s4} - v_{s3}$, the gain of the 2nd stage (v_{gs3}/v_{gs1}) is simply given by the ratio between the transistors transconductances g_{m1}/g_{m3} . Finally, considering that $v_o = v_o^+ - v_o^-$, the gain of the 3rd stage is given by,

$$\frac{v_o}{v_{gs3}} = g_{m3} \left(r_{o3} \parallel (sL_3 + r_3) \parallel \frac{1}{sC_L} \right) \quad (5)$$

r_3 is the inductor series resistance and C_L is the load capacitance. The resonance of the load of the LNA determines the LNA tuning frequency. This is determined by the load capacitance and inductance values. Neglecting r_3 , the LNA voltage gain is the product of the 3-stage voltage gains,

$$\frac{v_o}{v_x} \approx g_{m1} \frac{sL_3 r_{o3}}{r_{o3} + sL_3 + s^2 C_L L_3 r_{o3}} \frac{\sqrt{2}k}{1 + 2g_{m1}L_1(1 - 2k^2)s} \quad (6)$$

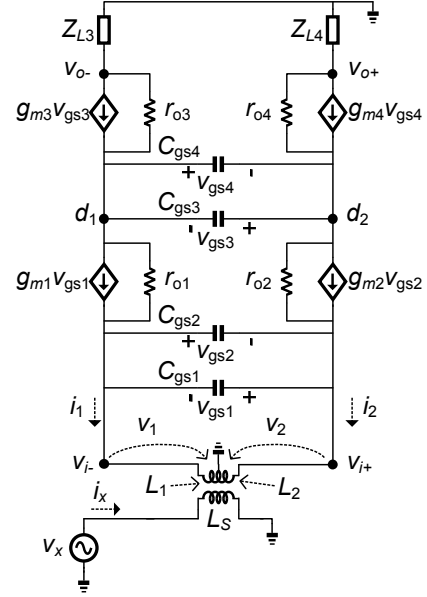


Fig. 2. Incremental model of the proposed LNA.

Noise Factor – The noise generated by M_1 and M_2 dominate the noise factor, F , of the LNA. Considering a perfect input impedance matching, i.e. $g_{m1} = g_{m2} = 1/R_S$, the LNA noise factor is,

$$F = 1 + \left| 1 - \varphi - \frac{Z_1 g_m}{1 + Z_1 g_m} \right|^2 \gamma, \quad (7)$$

where Z_1 is given by,

$$Z_1 = \frac{v_1}{i_1} = Ms - \frac{M^2 s^2}{R_S + L_S s} (1 - \varphi). \quad (8)$$

and φ is given by,

$$\varphi = \frac{sL_1(R_S + 2(1 - 2k^2)sL_1)}{R_S^2 + 3L_1 R_S s + 2(1 - 2k^2)L_1^2 s^2}. \quad (9)$$

One important feature of the CCC technique is that the noise due to transistors M_3 and M_4 is approximately canceled as shown in [1].

Imbalance Calculation – To determine the LNA phase and gain imbalances, the first step is to define the input signal. The input signal corresponds to the difference between the two balun output signals: v_{i+} and v_{i-} . Using v_{i+} as the reference, v_{i-} will correspond to the negation of v_{i+} multiplied by a complex number with gain and phase errors. The differential signal at the balun output is then,

$$v_i = v_{i+} - v_{i-} = (1 - (1 - \alpha)e^{j\beta})v_{i+}. \quad (10)$$

where α is the ratio between the amplitude of both signals and β is the phase error. As a note, the gain error is determined by $20\log(\alpha)$. Now we have to determine the signals at the drain of the two input stages,

TABLE I.
COMPONENT SIZES.

Parameter	Value	Parameter	Value
$(W/L)_{M1,M2}$	38.4/0.13	$L_S(R_S)$	4.0 nH (6 Ω)
$(W/L)_{M3,M4}$	32.0/0.13	$L_{\{1,2\}}(R_S)$	2.0 nH (3 Ω)
$R_{BIAS\{1,2,3,4\}}$	10 k Ω	$L_{\{3,4\}}(R_S)$	8.0 nH (12 Ω)
$C_{BIAS\{1,2,3,4\}}$	0.5 pF	k	0.9

$$\begin{cases} v_{d1} = g_{m1}Z_{load1}v_{in} \\ v_{d2} = g_{m2}Z_{load2}v_{in} \end{cases} \quad (11)$$

where g_{m2} is equal to xg_{m1} , and x accounts the mismatch between M_1 and M_2 . Z_{load1} and Z_{load2} are symmetrical, thus we will just determine Z_{load1} . Z_{load1} is a parallel of the following three impedances: the output impedance of M_1 : r_{o1} , the impedance made by M_3 : Z_{load13} , and the impedance made by M_4 : Z_{load14} . The expression of Z_{load1} is given by,

$$Z_{load1} = (r_{o1} // Z_{load13} // Z_{load14}), \quad (12)$$

where Z_{load13} and Z_{load14} are respectively,

$$\begin{cases} Z_{load13} \approx \left(\frac{1}{g_{m3}} // r_{o3} \right) + Z_{load3} \\ Z_{load14} \approx \frac{1}{s(C_{gs3} + C_{gs4})} + \left(\frac{1}{g_{m4}} // r_{o4} \right) + Z_{load4} \end{cases} \quad (13)$$

Both, Z_{load13} and Z_{load14} are obtained under the assumption that the impedance seen to the source of M_3 (M_4) is much smaller than that seen to the drain of M_1 (M_2) and Z_{load3} and Z_{load4} are given by,

$$Z_{load3} = Z_{load4} = Z_{load} = \left((sL_3 + r_{L3}) // \frac{1}{sC_3} \right), \quad (14)$$

where r_{L3} is the series resistance of L_3 . The differential voltage v_d is,

$$v_d = v_{d2} - v_{d1} = (Z_{load2}x - Z_{load1})g_{m1}v_i \quad (15)$$

We conclude from (15) that the imbalance just depends on the mismatches inside the circuit and is independent on the mismatches due to the balun. Finally, $v_o = v_{out+} - v_{out-}$ is obtained,

$$v_o = (g_{m3} - g_{m4})Z_{load}v_d = (1 - y)g_{m3}Z_{load}v_d \quad (16)$$

where $g_{m4} = yg_{m3}$. y accounts for the mismatch existing between M_3 and M_4 . From (16) we conclude that the phase and gain imbalance existing at the LNA output is only due to the mismatch between M_3 and M_4 . It implies that if M_3 and M_4 are purely matched and there is no channel length modulation, independently on the remaining circuit, the output imbalance can be nullified.

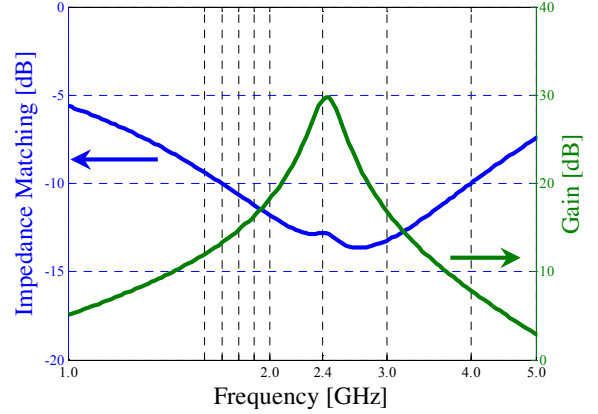


Fig. 3. Voltage gain and input impedance matching (S_{11}).

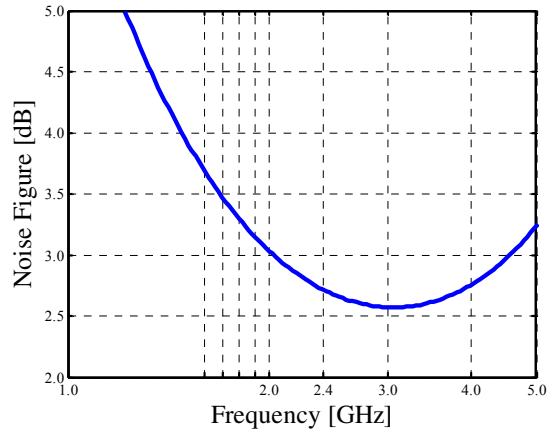


Fig. 4. Simulated noise figure.

IV. DESIGN VERIFICATION

A 1.2-V 2.4-GHz LNA design example with a 0.5-pF capacitive load is designed in 0.13- μ m CMOS. The associated component sizes are given in Table I. The balun coupling coefficient (k) is assumed to be 0.9, and the Q of all inductors is assumed to be 10 in practice, which defines their series resistance R_s at 2.4 GHz. The input impedance is matched with $R_s = 50 \Omega$ with $g_{m1} = g_{m2} = 1/R_s$. With 3 mW of power consumption, the achieved voltage gain, noise figure and input impedance matching (S_{11}) at 2.4 GHz are, respectively, 30 dB, 2.6 dB and -12.5 dB, as shown in Fig. 3. and Fig. 4, which are competitive values when compared to the state-of-the-art.

The output gain-phase balancing is accessed by varying the ratio between L_1 and L_2 as listed in Table II. For a phase error up to 10° and a gain error up to 2 dB (referred to the balun output) the LNA can adequately balance their outputs if the transistors are differentially matched. A simulation example is shown in Fig. 5 and Fig. 6 for the input-output gain and phase balancings, respectively. The LNA can tolerate up to 20% of transistor mismatch between the differential branches given such a gain-phase mismatch, which are easily manageable in modern technologies. Consequently, this circuit is highly

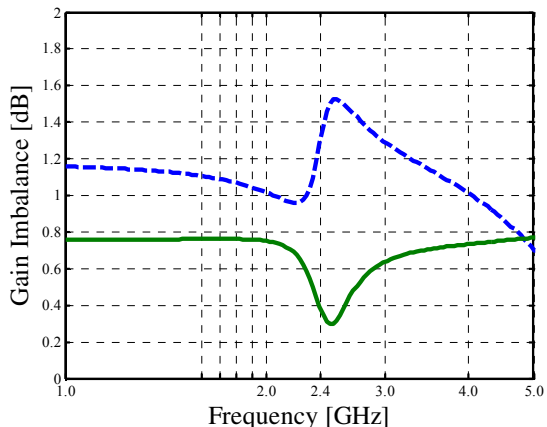


Fig. 5. LNA gain balancing capability example. Balun output inductance ratio of 1.3 and transistor differential mismatch (ratio between transistor widths) of 1.1.

----- Gain imbalance induced by the balun.
 ——— Gain imbalance after gain-phase balancing.

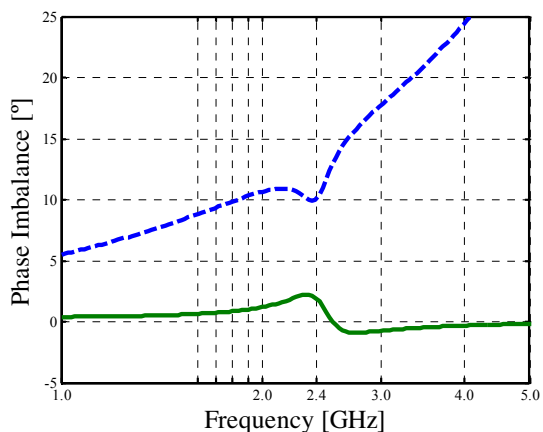


Fig. 6. LNA phase balancing capability example. Balun output inductance ratio of 1.3 and transistor differential mismatch (ratio between transistor widths) of 1.1.

----- Phase imbalance induced by the balun.
 ——— Phase imbalance after gain-phase balancing.

robust to the input differential imbalance induced by the balun.

The die size of the LNA using an integrated balun is $510 \mu\text{m} \times 750 \mu\text{m}$ including the bond pads (Fig. 7). The chip is currently under fabrication.

V. CONCLUSIONS

This paper introduced a new differential LNA with robust output gain-phase balancing. Two capacitive-cross-coupling common-gate amplifiers are in cascode to realize double gain-phase equalization. This topology not only realizes a high voltage gain with low noise through current-reuse g_m -enhancement, but also corrects robustly a wide range of input gain-phase imbalance under component mismatches. The feasibility has been demonstrated through the design of a 2.4-

Table II.
 LNA BALANCING CAPABILITY AT 2.4 GHz AGAINST
 BALUN IMBALANCE AND TRANSISTOR MISMATCH.

Balun Imbalance	Transistor Mismatch		Phase before & after balancing		Gain before & after balancing	
	L_1/L_2	W_{M1}/W_{M2}	W_{M3}/W_{M4}	$\Delta\Phi_{in}$ [°]	$\Delta\Phi_{out}$ [°]	ΔGain_{in} [dB]
1.1	1	1	2.57	0.03	0.48	0.01
1.3	1	1	7.73	0.09	1.32	0.04
1.3	1.1	1.1	8.92	1.56	0.98	0.38
1.3	1.2	1.2	9.63	2.93	0.69	0.65
1.4	1	1	10.32	0.12	1.69	0.05
1.4	1.2	1.2	12.42	2.98	1.03	0.66
1.4	1.3	1.3	12.78	4.25	0.78	0.86

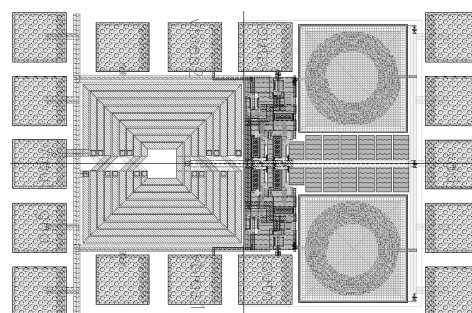


Fig. 7. Layout of the LNA.

GHz LNA, which can tolerate up to 2 dB and 10° gain and phase imbalances, respectively.

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